

**FEATURES**

**0.5  $\Omega$  Typical On Resistance**  
**0.8  $\Omega$  Maximum On Resistance at 125°C**  
**1.65 V to 3.6 V Operation**  
**Automotive Temperature Range: -40°C to +125°C**  
**High Current Carrying Capability: 300 mA Continuous**  
**Rail-to-Rail Switching Operation**  
**Fast Switching Times <20 ns**  
**Typical Power Consumption (<0.1  $\mu$ W)**

**APPLICATIONS**

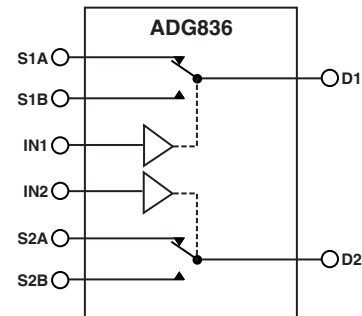
**Cellular Phones**  
**PDA's**  
**MP3 Players**  
**Power Routing**  
**Battery-Powered Systems**  
**PCMCIA Cards**  
**Modems**  
**Audio and Video Signal Routing**  
**Communication Systems**

**GENERAL DESCRIPTION**

The ADG836 is a low voltage CMOS device containing two independently selectable single-pole, double-throw (SPDT) switches. This device offers ultralow on resistance of less than 0.8  $\Omega$  over the full temperature range. The ADG836 is fully specified for 3.3 V, 2.5 V, and 1.8 V supply operation.

Each switch conducts equally well in both directions when on and has an input signal range that extends to the supplies. The ADG836 exhibits break-before-make switching action.

The ADG836 is available in 10-lead MSOP and 3 mm  $\times$  3 mm 12-lead LFCSP packages.

**FUNCTIONAL BLOCK DIAGRAM**


SWITCHES SHOWN FOR A LOGIC 1 INPUT

**PRODUCT HIGHLIGHTS**

1. <0.8  $\Omega$  over full temperature range of -40°C to +125°C.
2. Single 1.65 V to 3.6 V operation.
3. Compatible with 1.8 V CMOS logic.
4. High current handling capability (300 mA continuous current at 3.3 V).
5. Low THD + N (0.02% typ).
6. 3 mm  $\times$  3 mm LFCSP package and 10-lead MSOP package.

REV.0

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# ADG836—SPECIFICATIONS<sup>1</sup> ( $V_{DD} = 2.7\text{ V to }3.6\text{ V}$ , $GND = 0\text{ V}$ , unless otherwise noted.)

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
<b>ANALOG SWITCH</b>					
Analog Signal Range			0 V to $V_{DD}$	V	$V_{DD} = 2.7\text{ V}$
On Resistance ( $R_{ON}$ )	0.5			$\Omega$ typ	$V_{DD} = 2.7\text{ V}$ , $V_S = 0\text{ V to }V_{DD}$ , $I_S = 10\text{ mA}$ ;
	0.65	0.75	0.8	$\Omega$ max	Test Circuit 1
On Resistance Match between Channels ( $\Delta R_{ON}$ )	0.04			$\Omega$ typ	$V_{DD} = 2.7\text{ V}$ , $V_S = 0.65\text{ V}$ , $I_S = 10\text{ mA}$
		0.075	0.08	$\Omega$ max	
On Resistance Flatness ( $R_{FLAT(ON)}$ )	0.1			$\Omega$ typ	$V_{DD} = 2.7\text{ V}$ , $V_S = 0\text{ V to }V_{DD}$ ,
		0.15	0.16	$\Omega$ max	$I_S = 10\text{ mA}$
<b>LEAKAGE CURRENTS</b>					
Source Off Leakage $I_S$ (OFF)	$\pm 0.2$			nA typ	$V_{DD} = 3.6\text{ V}$
	$\pm 1$	$\pm 10$	$\pm 100$	nA max	$V_S = 0.6\text{ V}/3.3\text{ V}$ , $V_D = 3.3\text{ V}/0.6\text{ V}$ ;
Channel On Leakage $I_D$ , $I_S$ (ON)	$\pm 0.2$			nA typ	Test Circuit 2
	$\pm 1$	$\pm 15$	$\pm 120$	nA max	$V_S = V_D = 0.6\text{ V or }3.3\text{ V}$ ; Test Circuit 3
<b>DIGITAL INPUTS</b>					
Input High Voltage, $V_{INH}$			2	V min	
Input Low Voltage, $V_{INL}$			0.8	V max	
Input Current					
$I_{INL}$ or $I_{INH}$	0.005			$\mu\text{A}$ typ	$V_{IN} = V_{INL}$ or $V_{INH}$
			$\pm 0.1$	$\mu\text{A}$ max	
$C_{IN}$ , Digital Input Capacitance	4			pF typ	
<b>DYNAMIC CHARACTERISTICS<sup>2</sup></b>					
$t_{ON}$	21			ns typ	$R_L = 50\ \Omega$ , $C_L = 35\text{ pF}$
	26	28	29	ns max	$V_S = 1.5\text{ V}/0\text{ V}$ ; Test Circuit 4
$t_{OFF}$	4			ns typ	$R_L = 50\ \Omega$ , $C_L = 35\text{ pF}$
	7	8	9	ns max	$V_S = 1.5\text{ V}$ ; Test Circuit 4
Break-before-Make Time Delay ( $t_{BBM}$ )	17			ns typ	$R_L = 50\ \Omega$ , $C_L = 35\text{ pF}$
			5	ns min	$V_{S1} = V_{S2} = 1.5\text{ V}$ ; Test Circuit 5
Charge Injection	40			pC typ	$V_S = 1.5\text{ V}$ , $R_S = 0\ \Omega$ , $C_L = 1\text{ nF}$ ;
					Test Circuit 6
Off Isolation	-67			dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 100\text{ kHz}$ ;
					Test Circuit 7
Channel-to-Channel Crosstalk	-90			dB typ	S1A-S2A/S1B-S2B;
					$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 100\text{ kHz}$ ;
					Test Circuit 10
					S1A-S1B/S2A-S2B;
					$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 100\text{ kHz}$ ;
					Test Circuit 9
Total Harmonic Distortion (THD + N)	0.02			%	$R_L = 32\ \Omega$ , $f = 20\text{ Hz to }20\text{ kHz}$ ,
					$V_S = 2\text{ V p-p}$
Insertion Loss	-0.05			dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ ; Test Circuit 8
-3 dB Bandwidth	57			MHz typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ ; Test Circuit 8
$C_S$ (OFF)	25			pF typ	
$C_D$ , $C_S$ (ON)	75			pF typ	
<b>POWER REQUIREMENTS</b>					
$I_{DD}$	0.003			$\mu\text{A}$ typ	$V_{DD} = 3.6\text{ V}$
		1	4	$\mu\text{A}$ max	Digital Inputs = 0 V or 3.6 V

## NOTES

<sup>1</sup>Temperature range is as follows: Y version: -40°C to +125°C.

<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

# SPECIFICATIONS<sup>1</sup> ( $V_{DD} = 2.5 \text{ V} \pm 0.2 \text{ V}$ , $GND = 0 \text{ V}$ , unless otherwise noted.)

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
<b>ANALOG SWITCH</b>					
Analog Signal Range			0 V to $V_{DD}$	V	
On Resistance ( $R_{ON}$ )	0.65			$\Omega$ typ	$V_{DD} = 2.3 \text{ V}$ , $V_S = 0 \text{ V}$ to $V_{DD}$ , $I_S = 10 \text{ mA}$ ; Test Circuit 1
	0.72	0.8	0.88	$\Omega$ max	
On Resistance Match between Channels ( $\Delta R_{ON}$ )	0.04			$\Omega$ typ	$V_{DD} = 2.3 \text{ V}$ , $V_S = 0.7 \text{ V}$ ; $I_S = 10 \text{ mA}$
On Resistance Flatness ( $R_{FLAT(ON)}$ )	0.16	0.08	0.085	$\Omega$ max	
		0.23	0.24	$\Omega$ typ	$V_{DD} = 2.3 \text{ V}$ , $V_S = 0 \text{ V}$ to $V_{DD}$ , $I_S = 10 \text{ mA}$
				$\Omega$ max	
<b>LEAKAGE CURRENTS</b>					
Source Off Leakage $I_S$ (OFF)	$\pm 0.2$			nA typ	$V_{DD} = 2.7 \text{ V}$ $V_S = 0.6 \text{ V}/2.4 \text{ V}$ , $V_D = 2.4 \text{ V}/0.6 \text{ V}$ ; Test Circuit 2
	$\pm 0.4$	$\pm 4$	$\pm 45$	nA max	
Channel On Leakage $I_D$ , $I_S$ (ON)	$\pm 0.2$			nA typ	$V_S = V_D = 0.6 \text{ V}$ or $2.4 \text{ V}$ ; Test Circuit 3
	$\pm 0.6$	$\pm 12$	$\pm 90$	nA max	
<b>DIGITAL INPUTS</b>					
Input High Voltage, $V_{INH}$			1.7	V min	
Input Low Voltage, $V_{INL}$			0.7	V max	
Input Current $I_{INL}$ or $I_{INH}$	0.005			$\mu\text{A}$ typ	$V_{IN} = V_{INL}$ or $V_{INH}$
			$\pm 0.1$	$\mu\text{A}$ max	
$C_{IN}$ , Digital Input Capacitance	4			pF typ	
<b>DYNAMIC CHARACTERISTICS<sup>2</sup></b>					
$t_{ON}$	23			ns typ	$R_L = 50 \Omega$ , $C_L = 35 \text{ pF}$
	29	30	31	ns max	$V_S = 1.5 \text{ V}/0 \text{ V}$ ; Test Circuit 4
$t_{OFF}$	5			ns typ	$R_L = 50 \Omega$ , $C_L = 35 \text{ pF}$
	7	8	9	ns max	$V_S = 1.5 \text{ V}$ ; Test Circuit 4
Break-before-Make Time Delay ( $t_{BBM}$ )	17			ns typ	$R_L = 50 \Omega$ , $C_L = 35 \text{ pF}$
			5	ns min	$V_{S1} = V_{S2} = 1.5 \text{ V}$ ; Test Circuit 5
Charge Injection	30			pC typ	$V_S = 1.25 \text{ V}$ , $R_S = 0 \Omega$ , $C_L = 1 \text{ nF}$ ; Test Circuit 6
Off Isolation	-67			dB typ	$R_L = 50 \Omega$ , $C_L = 5 \text{ pF}$ , $f = 100 \text{ kHz}$ ; Test Circuit 7
Channel-to-Channel Crosstalk	-90			dB typ	S1A-S2A/S1B-S2B; $R_L = 50 \Omega$ , $C_L = 5 \text{ pF}$ , $f = 100 \text{ kHz}$ ; Test Circuit 10
				dB typ	S1A-S1B/S2A-S2B; $R_L = 50 \Omega$ , $C_L = 5 \text{ pF}$ , $f = 100 \text{ kHz}$ ; Test Circuit 9
Total Harmonic Distortion (THD + N)	0.022			%	$R_L = 32 \Omega$ , $f = 20 \text{ Hz}$ to $20 \text{ kHz}$ , $V_S = 1.5 \text{ V}$ p-p
Insertion Loss	-0.06			dB typ	$R_L = 50 \Omega$ , $C_L = 5 \text{ pF}$ ; Test Circuit 8
-3 dB Bandwidth	57			MHz typ	$R_L = 50 \Omega$ , $C_L = 5 \text{ pF}$ ; Test Circuit 8
$C_S$ (OFF)	25			pF typ	
$C_D$ , $C_S$ (ON)	75			pF typ	
<b>POWER REQUIREMENTS</b>					
$I_{DD}$	0.003			$\mu\text{A}$ typ	$V_{DD} = 2.7 \text{ V}$ Digital Inputs = 0 V or 2.7 V
		1.0	4.0	$\mu\text{A}$ max	

**NOTES**<sup>1</sup> Temperature range is as follows: Y version: -40°C to +125°C.<sup>2</sup> Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

# ADG836

## SPECIFICATIONS<sup>1</sup> ( $V_{DD} = 1.65\text{ V to }1.95\text{ V}$ , $GND = 0\text{ V}$ , unless otherwise noted.)

Parameter	+25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
<b>ANALOG SWITCH</b>					
Analogue Signal Range			0 V to $V_{DD}$	V	
On Resistance ( $R_{ON}$ )	1			$\Omega$ typ	$V_{DD} = 1.8\text{ V}$ , $V_S = 0\text{ V to }V_{DD}$ , $I_S = 10\text{ mA}$ ; Test Circuit 1
	1.4	2.2	2.2	$\Omega$ max	
	2	4	4	$\Omega$ max	$V_{DD} = 1.65\text{ V}$ , $V_S = 0\text{ V to }V_{DD}$ , $I_S = 10\text{ mA}$
On Resistance Match between Channels ( $\Delta R_{ON}$ )	0.1			$\Omega$ typ	$V_{DD} = 1.65\text{ V}$ , $V_S = 0.7\text{ V}$ , $I_S = 10\text{ mA}$
<b>LEAKAGE CURRENTS</b>					
Source Off Leakage $I_S$ (OFF)	$\pm 0.2$			nA typ	$V_{DD} = 1.95\text{ V}$ $V_S = 0.6\text{ V/1.65 V}$ , $V_D = 1.65\text{ V/0.6 V}$ ; Test Circuit 2
	$\pm 0.4$	$\pm 4$	$\pm 25$	nA max	
Channel On Leakage $I_D$ , $I_S$ (ON)	$\pm 0.2$			nA typ	$V_S = V_D = 0.6\text{ V or }1.65\text{ V}$ ; Test Circuit 3
	$\pm 0.6$	$\pm 10$	$\pm 75$	nA max	
<b>DIGITAL INPUTS</b>					
Input High Voltage, $V_{INH}$			$0.65 V_{DD}$	V min	
Input Low Voltage, $V_{INL}$			$0.35 V_{DD}$	V max	
Input Current $I_{INL}$ or $I_{INH}$	0.005			$\mu\text{A}$ typ	$V_{IN} = V_{INL}$ or $V_{INH}$
			$\pm 0.1$	$\mu\text{A}$ max	
$C_{IN}$ , Digital Input Capacitance	4			pF typ	
<b>DYNAMIC CHARACTERISTICS<sup>2</sup></b>					
$t_{ON}$	28			ns typ	$R_L = 50\ \Omega$ , $C_L = 35\text{ pF}$
	37	38	39	ns max	$V_S = 1.5\text{ V/0 V}$ ; Test Circuit 4
$t_{OFF}$	7			ns typ	$R_L = 50\ \Omega$ , $C_L = 35\text{ pF}$
	9	10	11	ns max	$V_S = 1.5\text{ V/0 V}$ ; Test Circuit 4
Break-before-Make Time Delay ( $t_{BBM}$ )	21			ns typ	$R_L = 50\ \Omega$ , $C_L = 35\text{ pF}$
			5	ns min	$V_{S1} = V_{S2} = 1\text{ V}$ ; Test Circuit 5
Charge Injection	20			pC typ	$V_S = 1\text{ V}$ , $R_S = 0\ \Omega$ , $C_L = 1\text{ nF}$ ; Test Circuit 6
Off Isolation	-67			dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 100\text{ kHz}$ ; Test Circuit 7
Channel-to-Channel Crosstalk	-90			dB typ	S1A-S2A/S1B-S2B; $R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 100\text{ kHz}$ ; Test Circuit 10
	-67			dB typ	S1A-S1B/S2A-S2B; $R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 100\text{ kHz}$ ; Test Circuit 9
Total Harmonic Distortion, THD	0.14			%	$R_L = 32\ \Omega$ , $f = 20\text{ Hz to }20\text{ kHz}$ , $V_S = 1.2\text{ V p-p}$
Insertion Loss	-0.08			dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ ; Test Circuit 8
-3 dB Bandwidth	57			MHz typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ ; Test Circuit 8
$C_S$ (OFF)	25			pF typ	
$C_D$ , $C_S$ (ON)	75			pF typ	
<b>POWER REQUIREMENTS</b>					
$I_{DD}$	0.003			$\mu\text{A}$ typ	$V_{DD} = 1.95\text{ V}$ Digital Inputs = 0 V or 1.95 V
		1.0	4	$\mu\text{A}$ max	

### NOTES

<sup>1</sup>Temperature range is as follows: Y version: -40°C to +125°C.

<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

## ABSOLUTE MAXIMUM RATINGS<sup>1</sup>

(T<sub>A</sub> = 25°C, unless otherwise noted.)

V <sub>DD</sub> to GND	−0.3 V to +4.6 V
Analog Inputs <sup>2</sup>	−0.3 V to V <sub>DD</sub> + 0.3 V
Digital Inputs <sup>2</sup>	−0.3 V to 4.6 V

or 10 mA, Whichever Occurs First

### Peak Current, S or D

3.3 V Operation	500 mA
2.5 V Operation	460 mA
1.8 V Operation	420 mA

(Pulsed at 1ms, 10% Duty Cycle Max)

### Continuous Current, S or D

3.3 V Operation	300 mA
2.5 V Operation	275 mA
1.8 V Operation	250 mA

### Operating Temperature Range

Automotive (Y Version) . . . . . −40°C to +125°C

Storage Temperature Range . . . . . −65°C to +150°C

Junction Temperature . . . . . 150°C

### MSOP Package

θ<sub>JA</sub> Thermal Impedance . . . . . 206°C/W

θ<sub>JC</sub> Thermal Impedance . . . . . 44°C/W

### LFCSP Package

θ<sub>JA</sub> Thermal Impedance (3-Layer Board) . . . . . 61.1°C/W

IR Reflow, Peak Temperature <20 sec . . . . . 235°C

### NOTES

<sup>1</sup> Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

<sup>2</sup> Overvoltages at IN, S, or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

**Table I. ADG836 Truth Table**

Logic	Switch A	Switch B
0	Off	On
1	On	Off

## ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option	Branding*
ADG836YRM	−40°C to +125°C	Mini Small Outline Package (MSOP)	RM-10	S9A
ADG836YRM-REEL	−40°C to +125°C	Mini Small Outline Package (MSOP)	RM-10	S9A
ADG836YRM-REEL7	−40°C to +125°C	Mini Small Outline Package (MSOP)	RM-10	S9A
ADG836YCP	−40°C to +125°C	Lead Frame Chip Scale Package (LFCSP)	CP-12	S9A
ADG836YCP-REEL	−40°C to +125°C	Lead Frame Chip Scale Package (LFCSP)	CP-12	S9A
ADG836YCP-REEL7	−40°C to +125°C	Lead Frame Chip Scale Package (LFCSP)	CP-12	S9A

\*Branding on this package is limited to three characters due to space constraints.

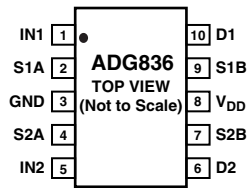
### CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG836 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.

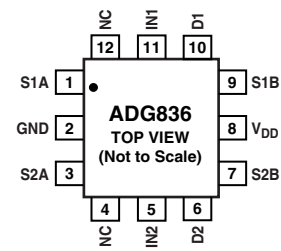


## PIN CONFIGURATIONS

**10-Lead MSOP  
(RM-10)**



**12-Lead LFCSP  
(CP-12)**

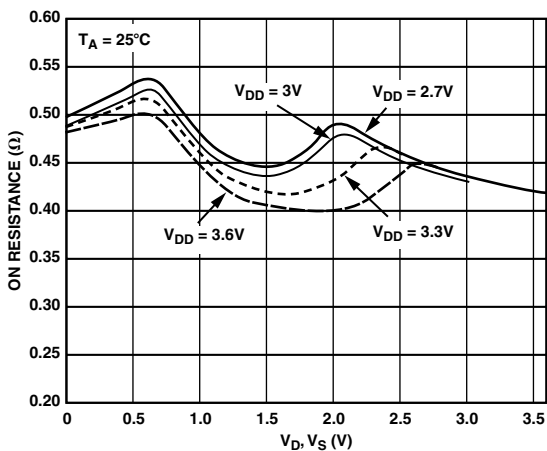


NC = NO CONNECT

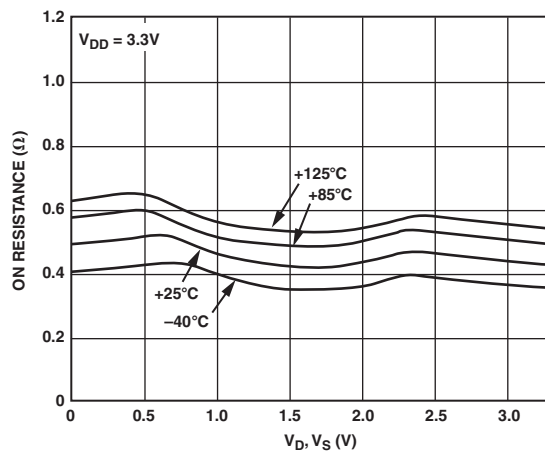
## TERMINOLOGY

$V_{DD}$	Most positive power supply potential.
$I_{DD}$	Positive supply current.
GND	Ground (0 V) reference.
S	Source terminal. May be an input or output.
D	Drain terminal. May be an input or output.
IN	Logic control input.
$V_D (V_S)$	Analog voltage on terminals D, S.
$R_{ON}$	Ohmic resistance between D and S.
$R_{FLAT (ON)}$	Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range.
$\Delta R_{ON}$	On resistance match between any two channels.
$I_S (OFF)$	Source leakage current with the switch off.
$I_D (OFF)$	Drain leakage current with the switch off.
$I_D, I_S (ON)$	Channel leakage current with the switch on.
$V_{INL}$	Maximum input voltage for Logic 0.
$V_{INH}$	Minimum input voltage for Logic 1.
$I_{INL} (I_{INH})$	Input current of the digital input.
$C_S (OFF)$	Off switch source capacitance. Measured with reference to ground.
$C_D (OFF)$	Off switch drain capacitance. Measured with reference to ground.
$C_D, C_S (ON)$	On switch capacitance. Measured with reference to ground.
$C_{IN}$	Digital input capacitance.
$t_{ON}$	Delay time between the 50% and the 90% points of the digital input and switch on condition.
$t_{OFF}$	Delay time between the 50% and the 90% points of the digital input and switch off condition.
$t_{BBM}$	On or off time measured between the 80% points of both switches when switching from one to another.
Charge Injection	A measure of the glitch impulse transferred from the digital input to the analog output during on-off switching.
Off Isolation	A measure of unwanted signal coupling through an off switch.
Crosstalk	A measure of unwanted signal which is coupled through from one channel to another as a result of parasitic capacitance.
-3 dB Bandwidth	The frequency at which the output is attenuated by 3 dB.
On Response	The frequency response of the on switch.
Insertion Loss	The loss due to the on resistance of the switch.
THD + N	The ratio of the harmonics amplitude plus noise of a signal, to the fundamental.

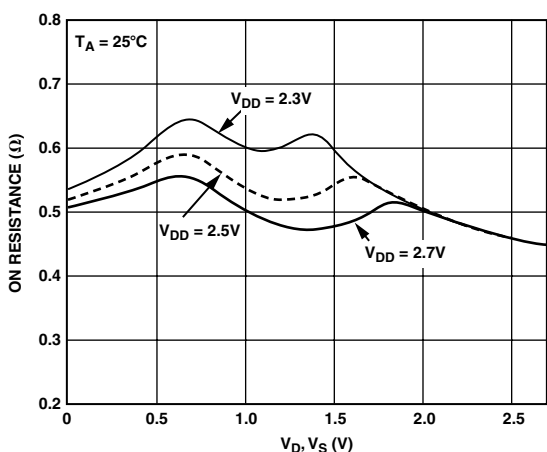
# Typical Performance Characteristics—ADG836



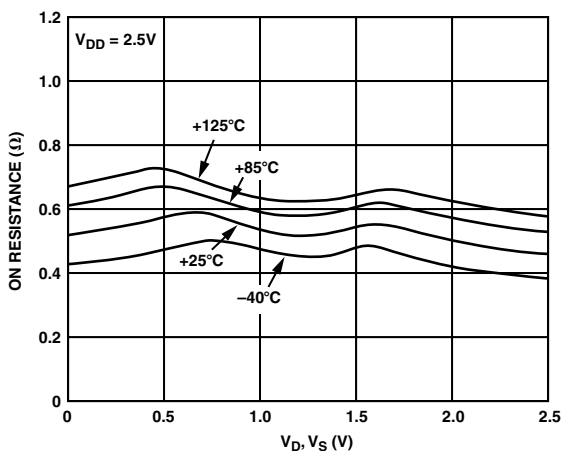
TPC 1. On Resistance vs.  $V_D$  ( $V_S$ )  $V_{DD} = 2.7V$  to  $3.6V$



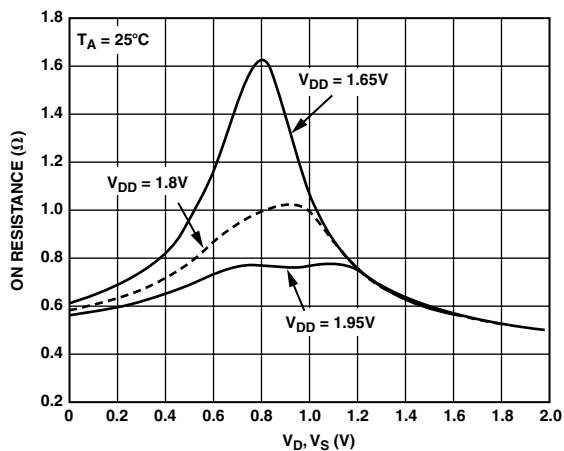
TPC 4. On Resistance vs.  $V_D$  ( $V_S$ ) for Different Temperatures,  $3.3V$



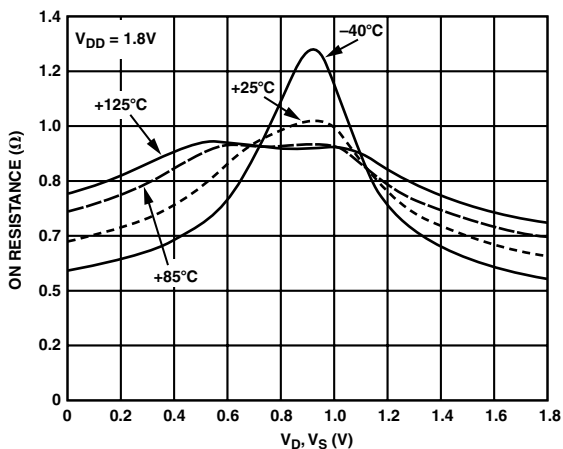
TPC 2. On Resistance vs.  $V_D$  ( $V_S$ )  $V_{DD} = 2.5V \pm 0.2V$



TPC 5. On Resistance vs.  $V_D$  ( $V_S$ ) for Different Temperature,  $2.5V$

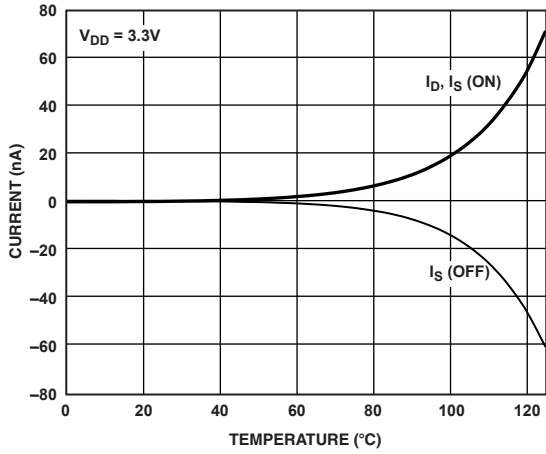


TPC 3. On Resistance vs.  $V_D$  ( $V_S$ ),  $V_{DD} = 1.8V \pm 0.15V$

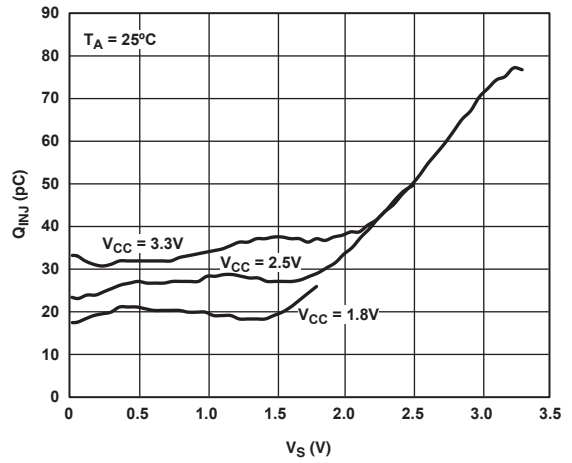


TPC 6. On Resistance vs.  $V_D$  ( $V_S$ ) for Different Temperatures,  $1.8V$

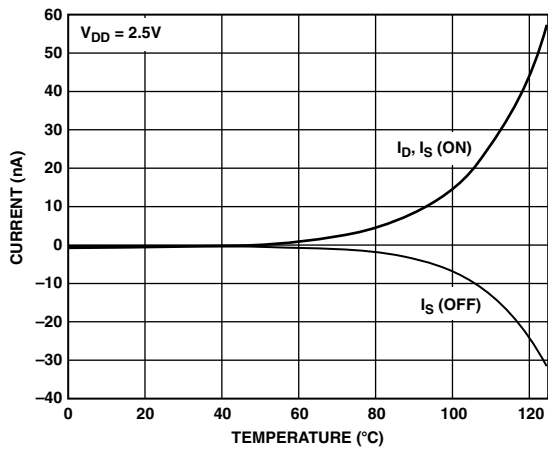
# ADG836



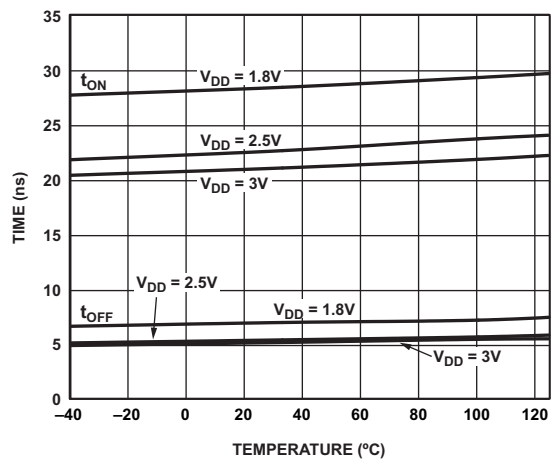
TPC 7. Leakage Currents vs. Temperature, 3.3 V



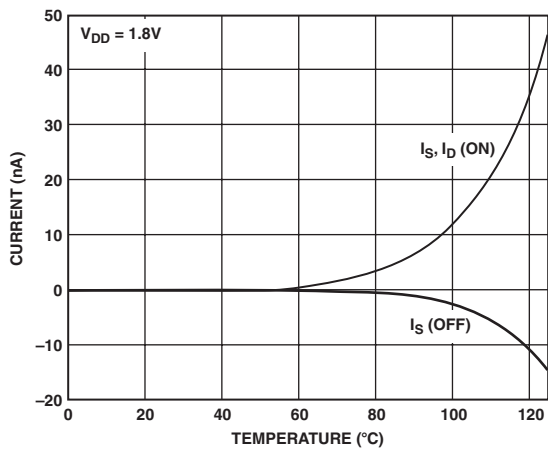
TPC 10. Charge Injection vs. Source Voltage



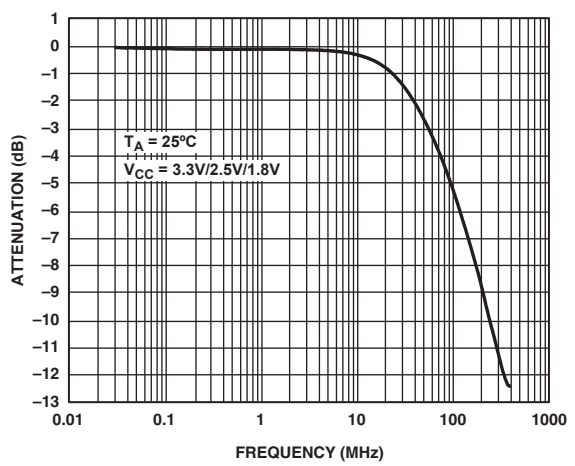
TPC 8. Leakage Current vs. Temperature, 2.5 V



TPC 11.  $t_{ON}/t_{OFF}$  Times vs. Temperature

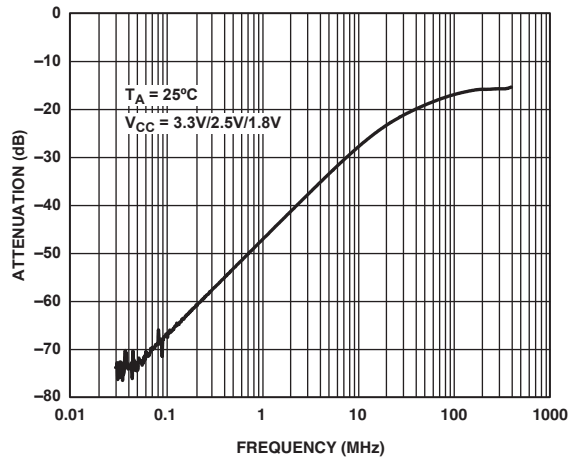


TPC 9. Leakage Current vs. Temperature, 1.8 V

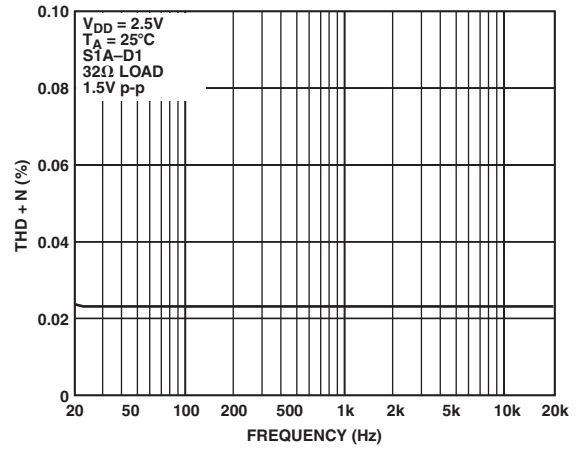


TPC 12. Bandwidth

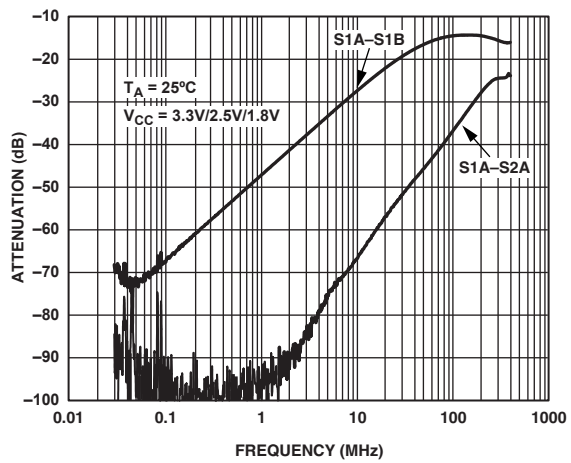




TPC 13. Off Isolation vs. Frequency



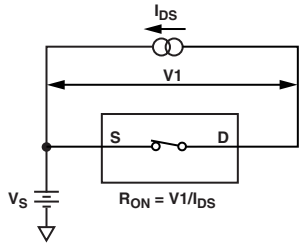
TPC 15. Total Harmonic Distortion + Noise



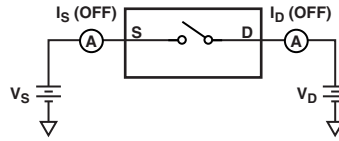
TPC 14. Crosstalk vs. Frequency

# ADG836

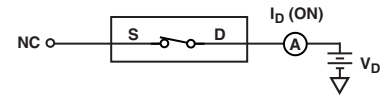
## Test Circuits



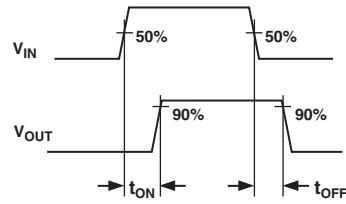
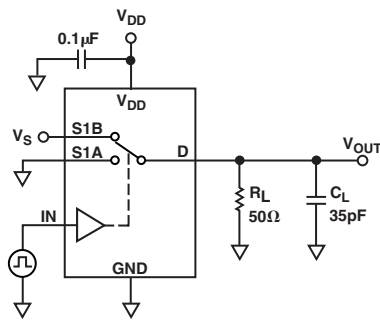
Test Circuit 1. On Resistance



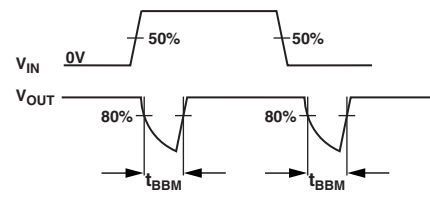
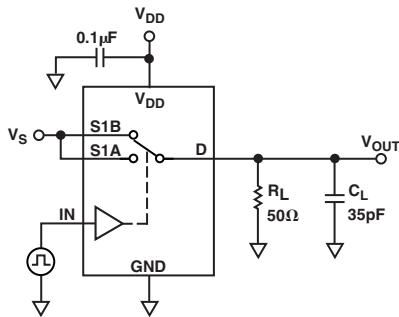
Test Circuit 2. Off Leakage



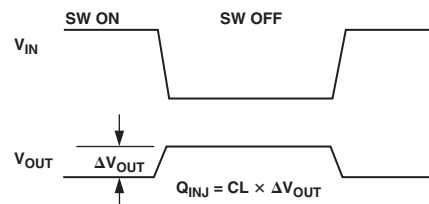
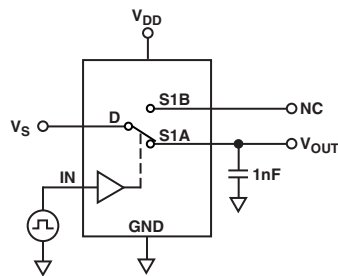
Test Circuit 3. On Leakage



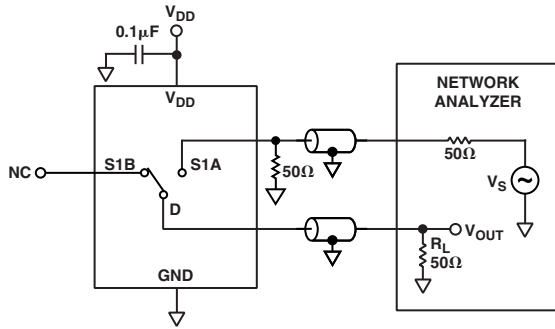
Test Circuit 4. Switching Times,  $t_{ON}$ ,  $t_{OFF}$



Test Circuit 5. Break-before-Make Time Delay,  $t_{BBM}$

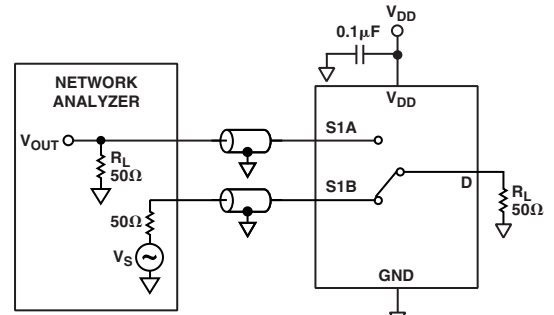


Test Circuit 6. Charge Injection



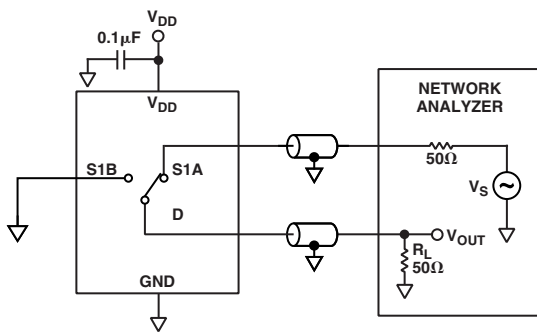
$$\text{OFF ISOLATION} = 20 \text{ LOG} \frac{V_{\text{OUT}}}{V_S}$$

Test Circuit 7. Off Isolation



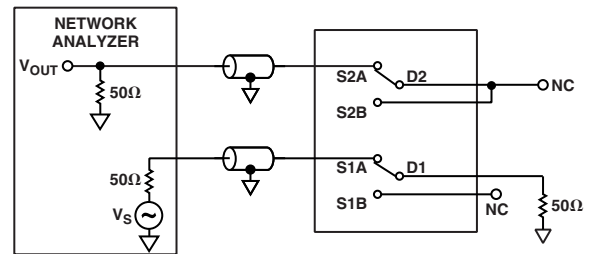
$$\text{CHANNEL-TO-CHANNEL CROSSTALK} = 20 \text{ LOG} \frac{V_{\text{OUT}}}{V_S}$$

Test Circuit 9. Channel-to-Channel Crosstalk (S1A-S1B)



$$\text{INSERTION LOSS} = 20 \text{ LOG} \frac{V_{\text{OUT WITH SWITCH}}}{V_{\text{OUT WITHOUT SWITCH}}}$$

Test Circuit 8. Bandwidth



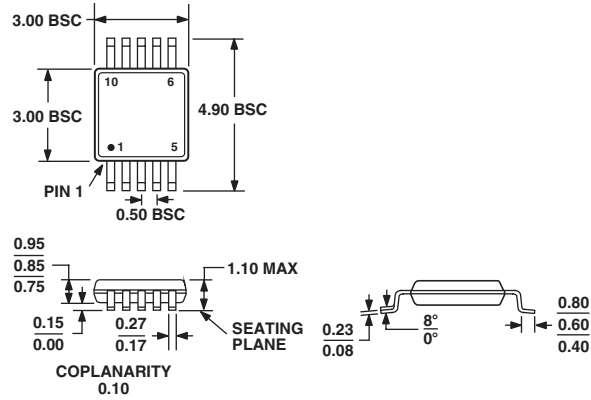
$$\text{CHANNEL-TO-CHANNEL CROSSTALK} = 20 \text{ LOG} \frac{V_{\text{OUT}}}{V_S}$$

Test Circuit 10. Channel-to-Channel Crosstalk (S1A-S2A)

OUTLINE DIMENSIONS

10-Lead Mini Small Outline Package [MSOP]  
(RM-10)

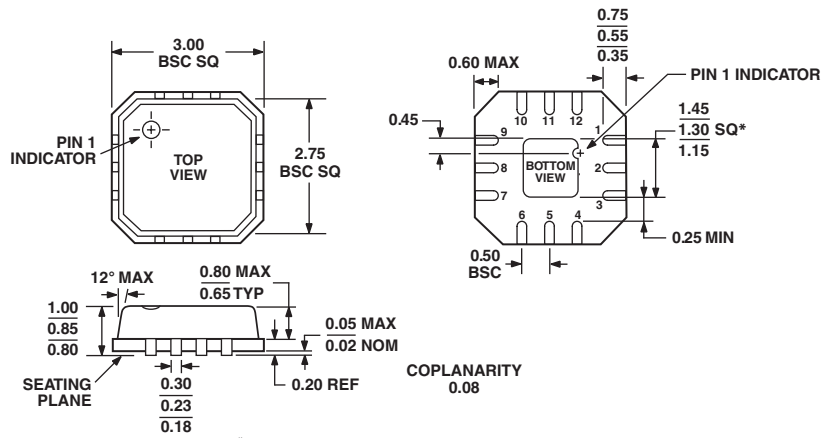
Dimensions shown in millimeters



COMPLIANT TO JEDEC STANDARDS MO-187BA

12-Lead Lead Frame Chip Scale Package [LFCSP]  
(CP-12)

Dimensions shown in millimeters



\*COMPLIANT TO JEDEC STANDARDS MO-220-VEED-1 EXCEPT FOR EXPOSED PAD DIMENSION

This datasheet has been download from:

[www.datasheetcatalog.com](http://www.datasheetcatalog.com)

Datasheets for electronics components.